

SDP8436

Silicon Phototransistor

FEATURES

- Side-looking plastic package
- 18° (nominal) acceptance angle
- Enhanced coupling distance
- Internal visible light rejection filter
- Low profile for design flexibility
- Wide sensitivity ranges
- Mechanically matched to SEP8736 infrared emitting diode



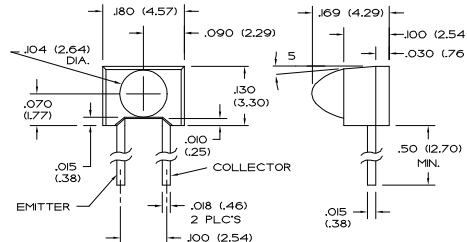
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DESCRIPTION

The SDP8436 is an NPN silicon phototransistor molded in a black plastic package which combines the mounting advantages of a side-looking package with the narrow acceptance angle and high optical gain of a T-1 package. The SDP8436 is designed for those applications which require longer coupling distances than standard side-looking devices can provide, such as touch screens. The device is also well suited to applications in which adjacent channel crosstalk could be a problem. The package is highly transmissive to the IR source energy while it provides effective shielding against visible ambient light.

OUTLINE DIMENSIONS in inches (mm)

Tolerance 3 plc decimals ±0.005(0.12)
2 plc decimals ±0.020(0.51)



DIM_019.dwg

SDP8436

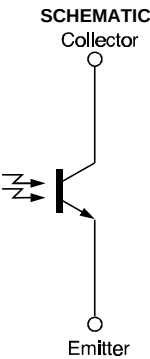
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ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)						
PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Light Current SDP8436-001 SDP8436-002 SDP8436-003 SDP8436-004	I_L	0.50 4.00 7.00 12.5		10.0 17.5	mA	$V_{CE}=5\text{ V}$ $H=1\text{ mW/cm}^2$ (1)
Collector Dark Current	I_{CEO}			100	nA	$V_{CE}=15\text{ V}$, $H=0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	30			V	$I_C=100\text{ }\mu\text{A}$
Emitter-Collector Breakdown Voltage	$V_{(BR)ECO}$	5.0			V	$I_E=100\text{ }\mu\text{A}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$			0.4	V	$I_C=0.1\text{ mA}$ $H=1\text{ mW/cm}^2$
Angular Response (2)	$\varnothing$		18		degr.	$I_F=\text{Constant}$
Rise And Fall Time	t_r, t_f		15		μs	$V_{CC}=5\text{ V}$, $I_L=1\text{ mA}$ $R_L=1000\text{ }\Omega$

Notes
1. The radiation source is an IRED with a peak wavelength of 880 nm.
2. Angular response is defined as the total included angle between the half sensitivity points.

ABSOLUTE MAXIMUM RATINGS	
(25°C Free-Air Temperature unless otherwise noted)	
Collector-Emitter Voltage	30 V
Emitter-Collector Voltage	5 V
Power Dissipation	100 mW (1)
Operating Temperature Range	-40°C to 85°C
Storage Temperature Range	-40°C to 85°C
Soldering Temperature (5 sec)	240°C

Notes
1. Derate linearly from 25°C free-air temperature at the rate of 0.78 mW/°C.



Honeywell reserves the right to make changes in order to improve design and supply the best products possible.

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SWITCHING TIME TEST CIRCUIT

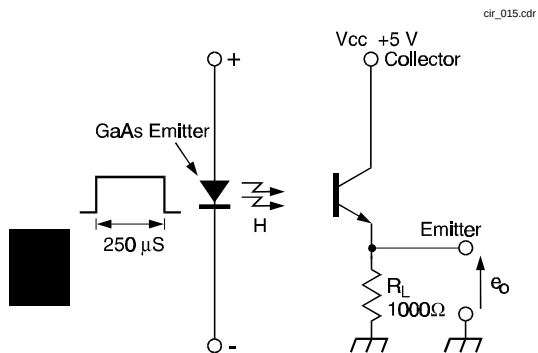


Fig. 1 Responsivity vs Angular Displacement

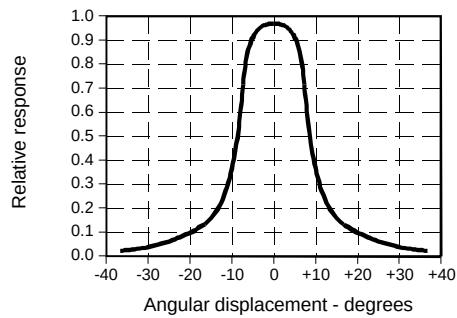
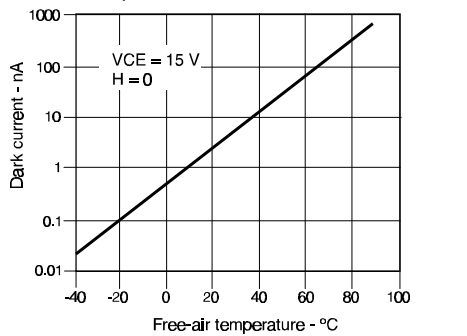


Fig. 3 Dark Current vs Temperature



SWITCHING WAVEFORM

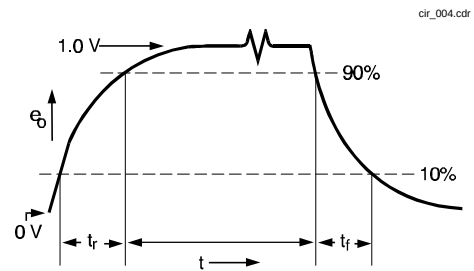


Fig. 2 Collector Current vs Ambient Temperature

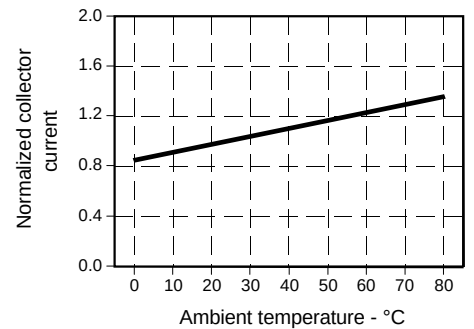
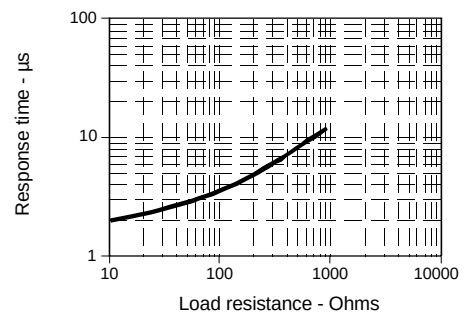


Fig. 4 Non-Saturated Switching Time vs Load Resistance



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Fig. 5 Spectral Responsivity

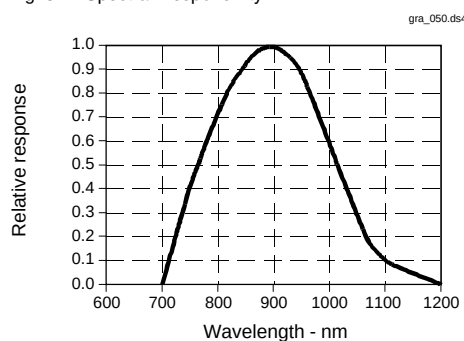
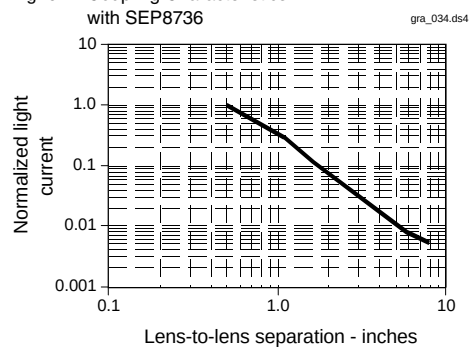


Fig. 6 Coupling Characteristics with SEP8736



All Performance Curves Show Typical Values